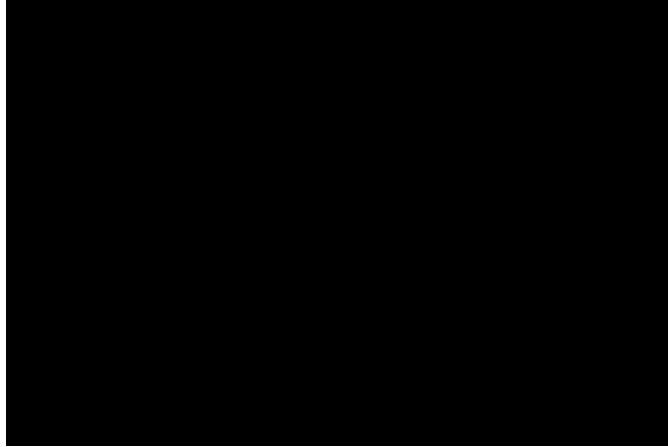
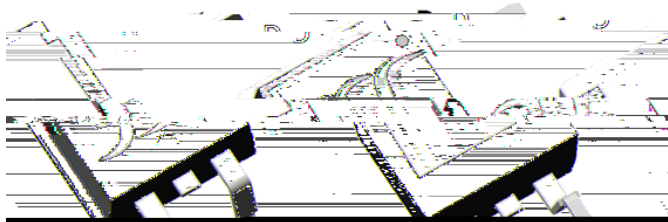




# YJB17C80HJ

## N-Channel Enhancement Mode Field Effect Transistor



### Product Summary

$V_{DS}$	800V
$I_D$	17A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	290m
100% EAS Tested	
100% $V_{DS}$ Tested	

### General Description

Super Junction High Voltage MOSFET technology  
 Low Power Loss by High Speed Switching and  
 Low On-Resistance  
 Moisture Sensitivity Level 1  
 Epoxy Meets UL 94 V-0 Flammability Rating  
 Halogen Free

### Applications

Power switching application  
 Flyback power supply stages  
 Adapter  
 Lighting

### Absolute Maximum Ratings ( $T_A=25$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	800	V
Gate-source Voltage		$V_{GS}$	$\pm 30$	V
Drain Current	$T_A=25$	$I_D$	2	A
	$T_A=100$		1.3	
	$T_C=25$		17	
	$T_C=100$		10	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	50	A
Avalanche energy <sup>B</sup>		EAS	225	mJ
Total Power Dissipation <sup>C</sup>	$T_A=25$	$P_D$	2.7	W
	$T_A=100$		1	
	$T_C=25$		200	
	$T_C=100$		80	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 +150	

### Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>D</sup>	Steady-State	$R_{JA}$	35	45	/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{JC}$	0.5	0.62	

### Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJB17C80HJ	F2	YJB17C80HJ	800	/	8000	13" reel







# YJB17C80HJ

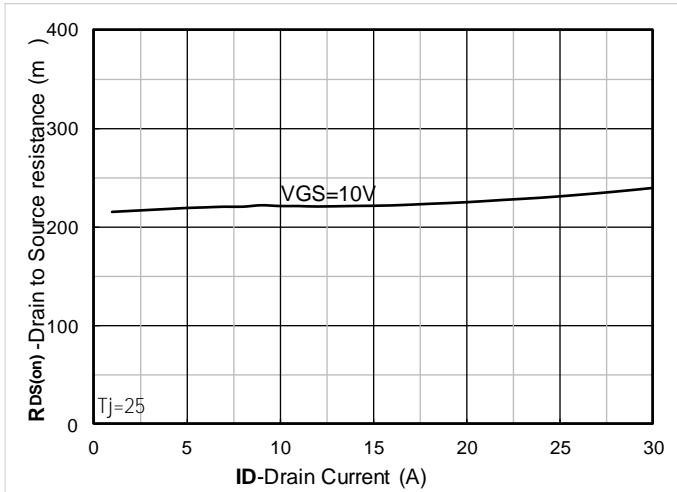


Figure7. RDS(on) VS Drain Current

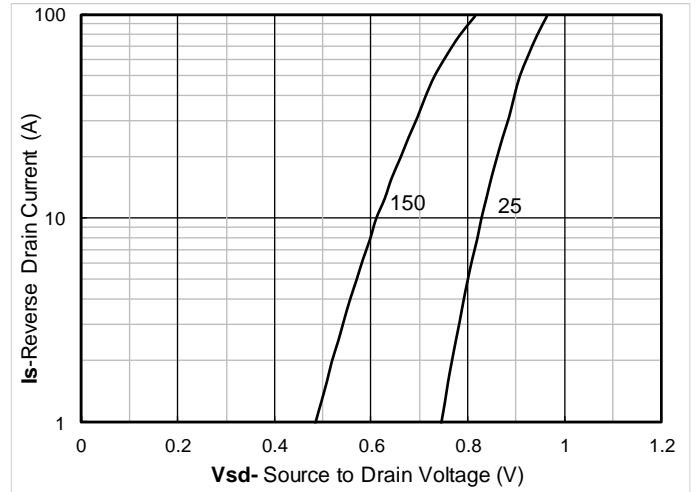


Figure8. Forward characteristics of reverse diode

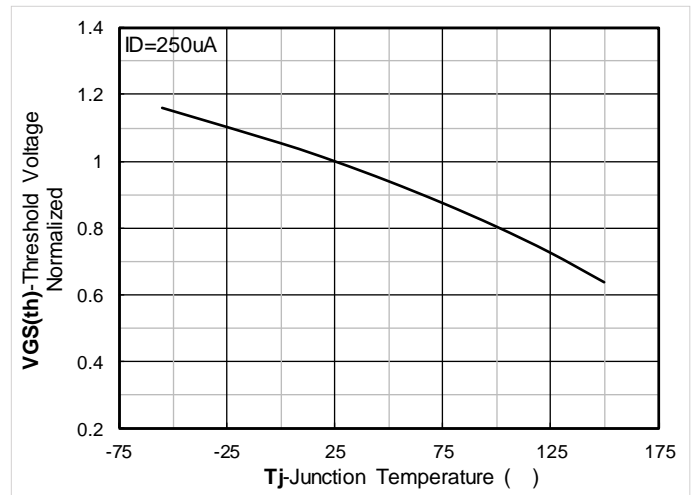


Figure9. Normalized breakdown voltage

Figure10. Normalized Threshold voltage

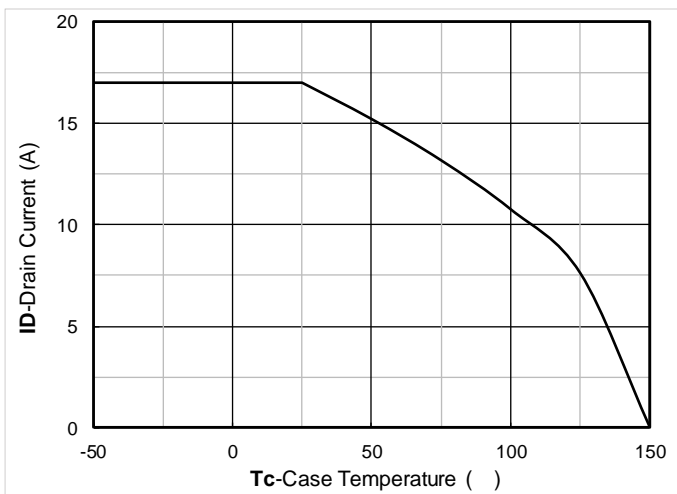


Figure11. Current dissipation

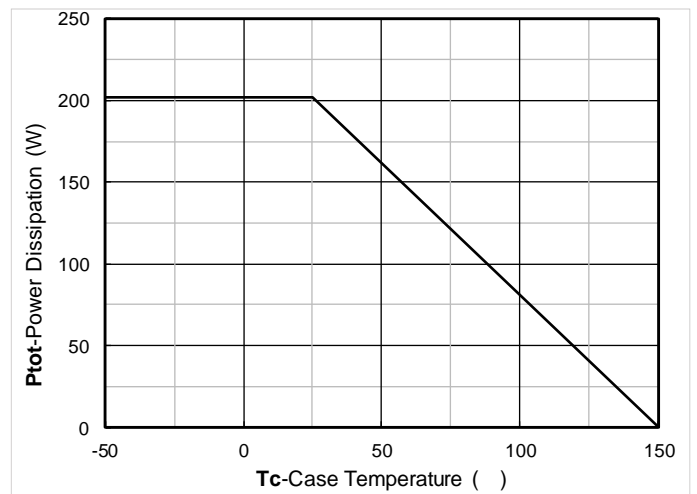


Figure12. Power dissipation





TO-263-HY Package information

SYM.	MIN.	
A2		
b2		0.050
c		
c2		
D2		
E		
E1		

